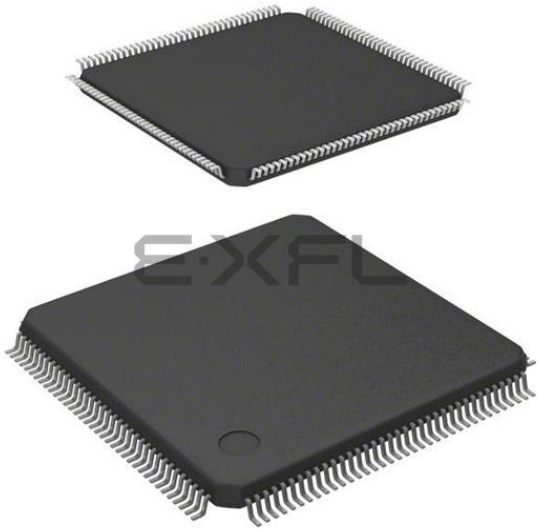

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What is "Embedded - Microcontrollers"?

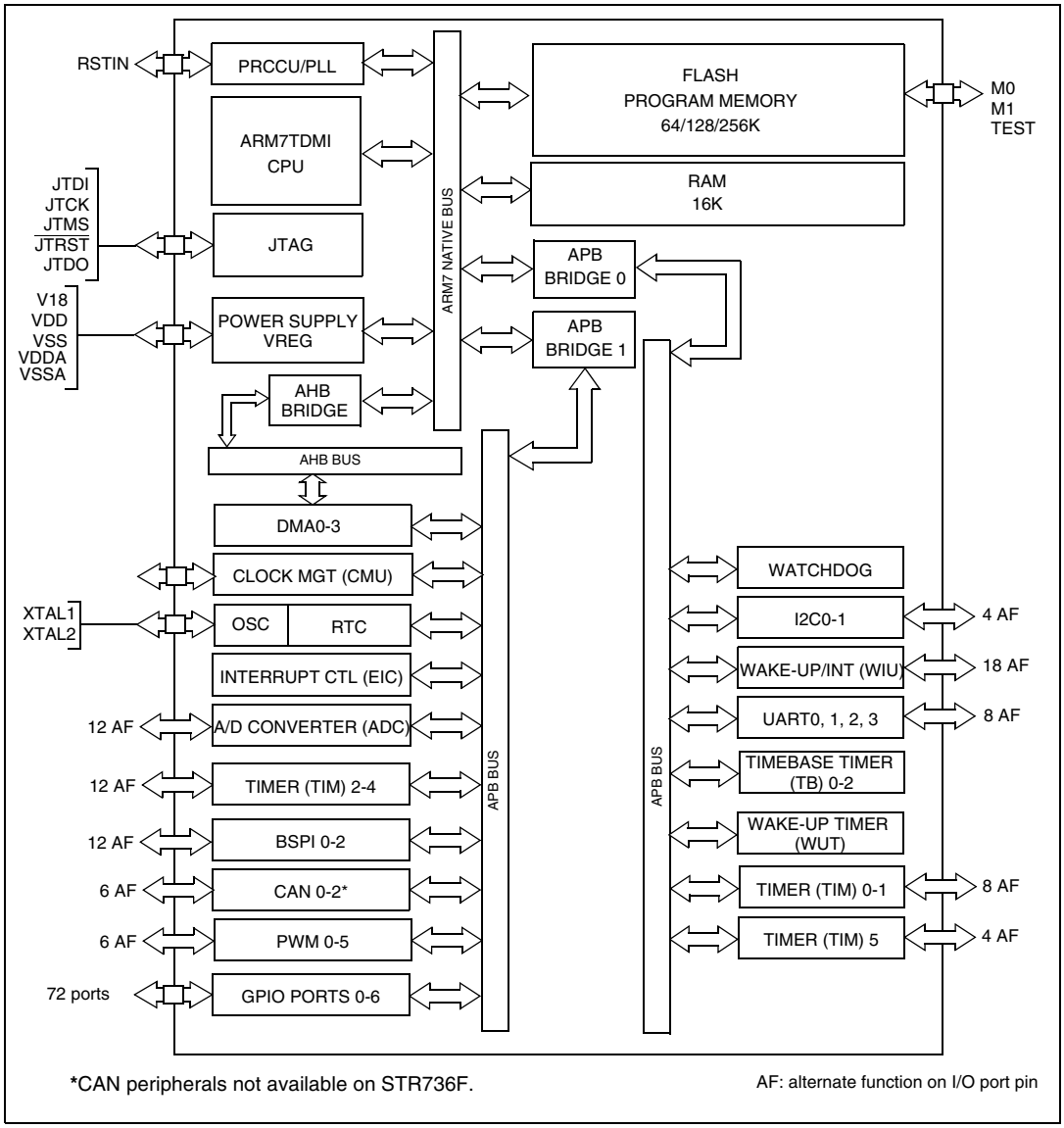
"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM7®
Core Size	32-Bit Single-Core
Speed	36MHz
Connectivity	I²C, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	112
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	4.5V ~ 5.5V
Data Converters	A/D 16x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/str735fz2t7

Contents

Figure 2. STR731F/STR736 block diagram



*CAN peripherals not available on STR736F.

AF: alternate function on I/O port pin

3.1 Related documentation

Available from www.arm.com:

ARM7TDMI technical reference manual

Available from http://www.st.com:

STR73x reference manual (RM0001)

STR7 Flash programming reference manual

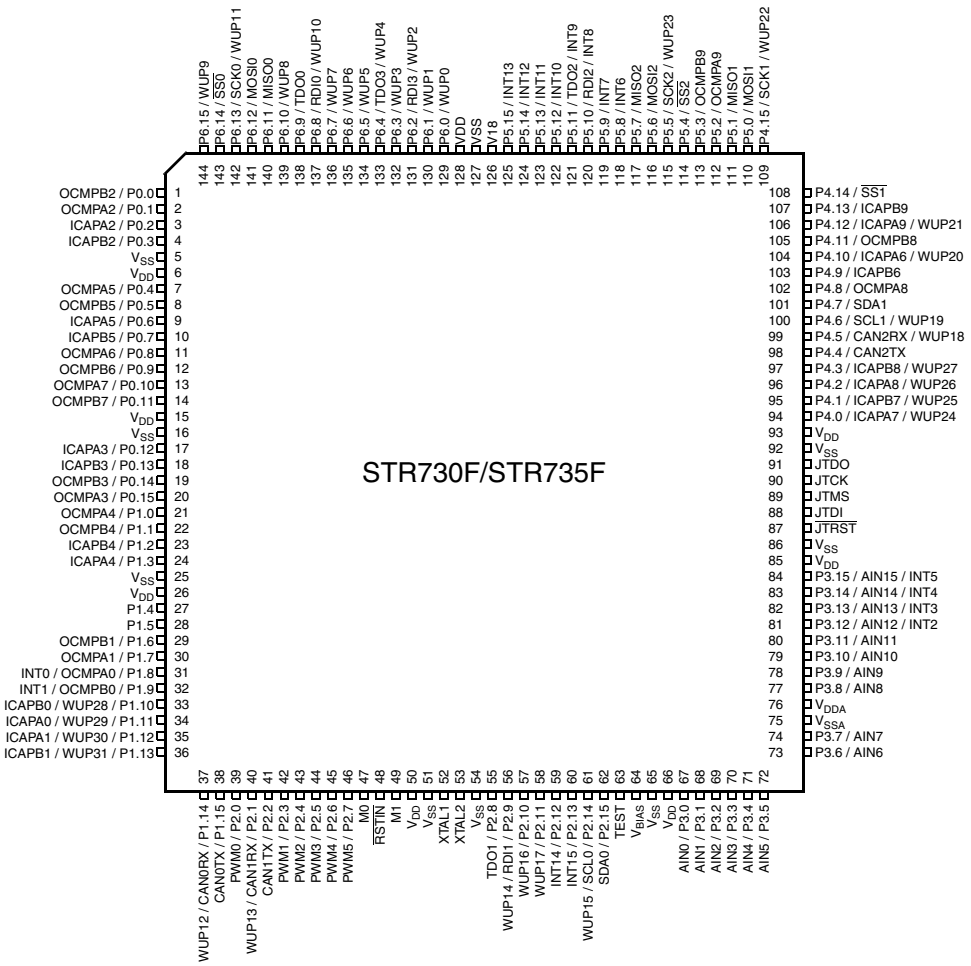
STR73x software library user manual

For a list of related application notes refer to http://www.st.com.

3.2 Pin description

3.2.1 STR730F/STR735F (TQFP144)

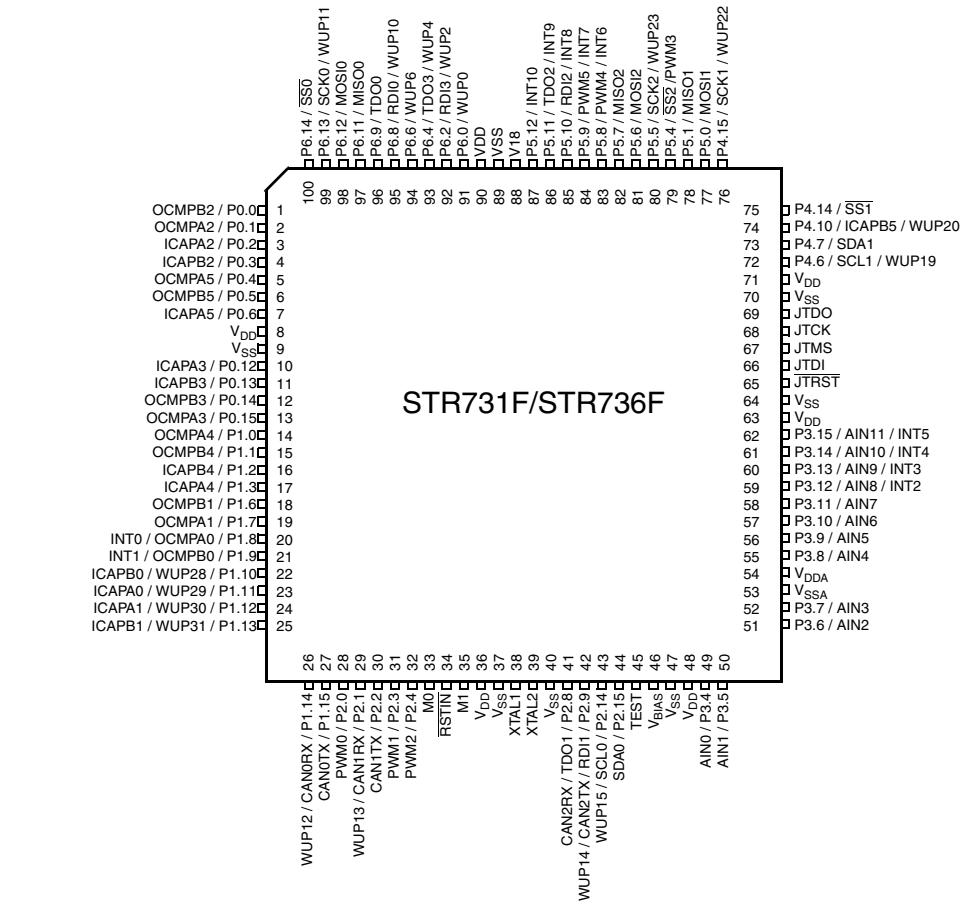
Figure 3. STR730F/STR735F pin configuration (top view)



Note: CAN alternate functions not available on STR735F.

3.2.3 STR731F/STR736F (TQFP100)

Figure 4. STR731F/STR736F pin configuration (top view)



Note: CAN alternate functions not available on STR736F.

Table 4. STR73xF pin description

Pin n°			Pin name	Type	Input			Output			Main function (after reset)	Alternate function
TQFP144	LFBGA144	TQFP100			Input Level	pu/pd	interrupt	Capability	OD	PP		
19	F3	12	P0.14/OCMPB3	I/O	T_T			2mA	X	X	Port 0.14	TIM3: output compare B output
20	F4	13	P0.15/OCMPA3	I/O	T_T			2mA	X	X	Port 0.15	TIM3: output compare A output
21	F5	14	P1.0/OCMPA4	I/O	T_T			2mA	X	X	Port 1.0	TIM4: output compare A output
22	F6	15	P1.1/OCMPB4	I/O	T_T			2mA	X	X	Port 1.1	TIM4: output compare B output
23	G2	16	P1.2/ICAPB4	I/O	T_T			2mA	X	X	Port 1.2	TIM4: input capture B input
24	G3	17	P1.3/ICAPA4	I/O	T_T			2mA	X	X	Port 1.3	TIM4: input capture A input
25	G4		V_{SS}	S							Ground	
26	H1		V_{DD}	S							Supply voltage (5 V)	
27	J1		P1.4	I/O	T_T			2mA	X	X	Port 1.4	
28	G5		P1.5	I/O	T_T			2mA	X	X	Port 1.5	
29	K1	18	P1.6/OCMPB1	I/O	T_T			2mA	X	X	Port 1.6	TIM1: output compare B output
30	L1	19	P1.7/OCMPA1	I/O	T_T			2mA	X	X	Port 1.7	TIM1: output compare A output
31	H2	20	P1.8/OCMPA0	I/O	T_T		INT0	2mA	X	X	Port 1.8	TIM0: output compare A output
32	H3	21	P1.9/OCMPB0	I/O	T_T		INT1	2mA	X	X	Port 1.9	TIM0: output compare B output
33	H4	22	P1.10/ICAPB0	I/O	T_T		WUP28	2mA	X	X	Port 1.10	TIM0: input capture B input
34	J2	23	P1.11/ICAPA0	I/O	T_T		WUP29	2mA	X	X	Port 1.11	TIM0: input capture A input
35	J3	24	P1.12/ICAPA1	I/O	T_T		WUP30	2mA	X	X	Port 1.12	TIM1: input capture A input
36	K2	25	P1.13/ICAPB1	I/O	T_T		WUP31	2mA	X	X	Port 1.13	TIM1: input capture B input
37	M1	26	P1.14/CAN0RX	I/O	T_T		WUP12	2mA	X	X	Port 1.14	CAN0: receive data input
38	L2	27	P1.15/CAN0TX	I/O	T_T			2mA	X	X	Port 1.15	CAN0: transmit data output
39	L3	28	P2.0/PWM0	I/O	T_T			2mA	X	X	Port 2.0	PWM0: PWM output
40	K3	29	P2.1/CAN1RX	I/O	T_T		WUP13	2mA	X	X	Port 2.1	CAN1: receive data input
41	M4	30	P2.2/CAN1TX	I/O	T_T			2mA	X	X	Port 2.2	CAN1: transmit data output
42	L4	31	P2.3/PWM1	I/O	T_T			2mA	X	X	Port 2.3	PWM1: PWM output
43	M2	32	P2.4/PWM2	I/O	T_T			2mA	X	X	Port 2.4	PWM2: PWM output
44	M3		P2.5/PWM3	I/O	T_T			2mA	X	X	Port 2.5	PWM3: PWM output
45	K4		P2.6/PWM4	I/O	T_T			2mA	X	X	Port 2.6	PWM4: PWM output
46	J4		P2.7/PWM5	I/O	T_T			2mA	X	X	Port 2.7	PWM5: PWM output
47	M5	33	M0	I	T_T	pd					BOOT: mode selection 0 input	
48	L5	34	RSTIN	I	C_T	pu					Reset input	
49	K5	35	M1	I	T_T	pd					BOOT: mode selection 1 input	

4 Electrical parameters

4.1 Parameter conditions

Unless otherwise specified, all voltages are referred to V_{SS}.

4.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A=25° C and T_A=T_{Amax} (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3Σ).

4.1.2 Typical values

Unless otherwise specified, typical data are based on T_A=25° C and V_{DD}=5 V. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean±2Σ).

4.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

4.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 6*.

4.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 7*.

Figure 6. Pin loading conditions

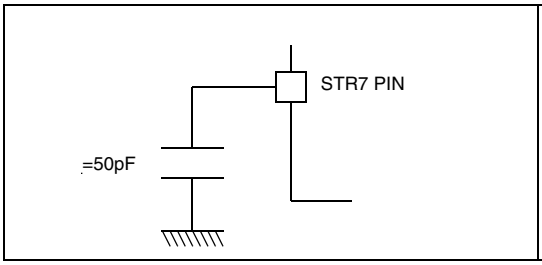
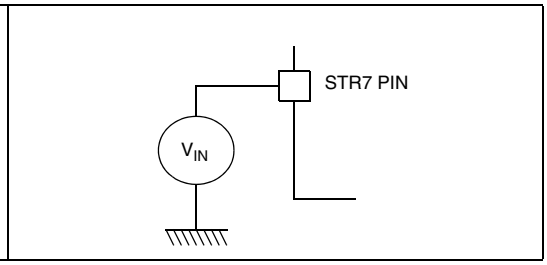


Figure 7. Pin input voltage



4.2 Absolute maximum ratings

Stresses above those listed as “absolute maximum ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device under these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 5. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
V_{DD} - V_{SS}	External 5 V Supply voltage	-0.3	6.0	V
V_{SSA}	Reference ground for A/D converter	V_{SS}	V_{SS}	V
V_{DDA}- V_{SSA}	Reference voltage for A/D converter	-0.3	V_{DD}+0.3	V
V_{IN}	Input voltage on any pin	-0.3	V_{DD}+0.3	
$\lvert\Delta V_{DDx}\rvert$	Variations between different 5 V power pins	-	0.3	mV
$\lvert V_{SSX}$ - $V_{SS}\rvert$	Variations between all the different ground pins	-	0.3	
$V_{ESD(HBM)}$	Electrostatic discharge voltage (Human Body Model)	see *: Absolute maximum ratings (electrical sensitivity) on page 36*		
$V_{ESD(MM)}$	Electrostatic discharge voltage (Machine Model)			

Table 6. Current characteristics

Symbol	Ratings	Max.	Unit
I_{VDD}	Total current into V_{DD} power lines (source) 1)	100	mA
I_{VSS}	Total current out of V_{SS} ground lines (sink) 1)	100	
I_{IO}	Output current sunk by any I/O and control pin	10	
	Output current source by any I/O and control pin	10	
$I_{INJ(PIN)}$ 2) & 3)	Injected current on any other pin 4) &5)	±10	
$\Sigma I_{INJ(PIN)}$ 2)	Total injected current (sum of all I/O and control pins) 4)	±75	

1. All 5 V power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external 5 V supply
2. $I_{INJ(PIN)}$ must never be exceeded. This is implicitly insured if V_{IN} maximum is respected. If V_{IN} maximum cannot be respected, the injection current must be limited externally to the $I_{INJ(PIN)}$ value. A positive injection is induced by $V_{IN}>V_{DD}$ while a negative injection is induced by $V_{IN}<V_{SS}$.
3. Negative injection disturbs the analog performance of the device. See note in *Section 4.3.6: 10-bit ADC characteristics on page 43*.
4. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values). These results are based on characterization with $\Sigma I_{INJ(PIN)}$ maximum current injection on four I/O port pins of the device.

5.) In 144-pin devices, only +10 mA on P0.3, P1.13, P3.6 and P4.13 pins (negative injection not allowed).

Table 7. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	-55 to +150	°C
T_J	Maximum junction temperature (see *Section 5.2: Thermal characteristics on page 48*)		

4.3 Operating conditions

Subject to general operating conditions for V_{DD}, and T_A.

Table 8. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCLK}	Internal CPU and system clock frequency	Accessing SRAM or Flash (zero wait state Flash access up to 36 MHz)	0	36	MHz
V_{DD}	Standard Operating Voltage		4.5	5.5	V
V_{DDA}	Operating analog reference voltage with respect to ground		4.5	V_{DD}+0.1	V
T_A	Ambient temperature range	6 partnumber suffix 7 partnumber suffix	-40 -40	85 105	°C

Table 9. Operating conditions at power-up / power-down

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{VDD}	V_{DD} rise time rate	Subject to general operating conditions for T_A.	-	20	-	ms/V

4.3.1 Supply current characteristics

The current consumption is measured as described in *Figure 6* and *Figure 7*.

Total current consumption

The MCU is placed under the following conditions:

- All I/O pins in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled except if explicitly mentioned.

Subject to general operating conditions for V_{DD}, and T_A.

Table 10. Total current consumption

Symbol	Parameter	Conditions	Typ [1]	Max [2]	Unit
I_{DD}	RUN mode[3]	Formula, f_{MCLK} in MHz, RAM execution	7 + 1.9 f_{MCLK}		mA
		f_{MCLK} = 36 MHz, RAM execution	76		mA
		f_{MCLK} = 36 MHz, Flash execution	86		mA
	WFI mode	f_{OSC} = 4 MHz, f_{MCLK}= f_{OSC}/16 = 250 kHz Main voltage regulator ON, LP voltage regulator = 2 mA, RTC and WDG on, other modules off.	6.7	8	mA
	LPWFI mode	f_{RC} = high frequency (CMU_RCCTL= 0x8), f_{MCLK}= f_{RC} /16, LP voltage regulator = 2 mA, other modules off.	220	350	µA
	STOP mode	f_{OSC} = 4 MHz, RC oscillator on f_{RC} = high frequency (CMU_RCCTL= 0x0) LP voltage regulator = 6 mA, RTC and WUT ON, other modules off. Internal wake-up possible.	500	700	µA
		f_{RC} = high frequency (CMU_RCCTL= 0xF), LP voltage regulator = 2mA. WUT ON, other modules off. Internal wake-up possible.	150	220	
		LP voltage regulator = 2 mA, WIU on, Other modules off, external wake-up.	50	140	
	HALT mode	LP voltage regulator = 2 mA.	50	140	µA

1. Typical data are based on T_A=25° C, V_{DD}=5 V
2. Data based on characterization results, tested in production at V_{DD} max. and T_A = 25° C.
3. I/O in static configuration (not toggling). RUN mode is almost **independent of temperature**. On the contrary RUN mode current is **highly dependent on the application**. The I_{DDRUN} value can be significantly reduced by the application in the following ways: switch-off unused peripherals (default), reduce peripheral frequency through internal prescaler, fetch the most frequently-used functions from RAM and use low power mode when possible.

Main oscillator characteristics

V_{DD} = 5 V ± 10%, T_A = -40° C to T_{Amax}, unless otherwise specified.

Table 14. Main oscillator characteristics

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
f_{OSC}	Oscillator frequency		4		8	MHz
g_m	Oscillator transconductance		1.5		4.2	mA/V
V_{OSC} 1)	Oscillation amplitude	f_{OSC} = 4 MHz, T_A= 25° C	-	2.4	-	V
		f_{OSC} = 8 MHz, T_A= 25° C		1.-		
V_{AV} 1)	Oscillator operating point	Sine wave middle, T_A= 25° C	-	0.77	-	v
t_{STUP} 1)	Oscillator start-up time	External crystal, V_{DD} = 5.5 V, f_{OSC} = 4 MHz, T_A=-40° C	-	-	12	ms
		External crystal, V_{DD} = 5.0 V, f_{OSC} = 4 MHz, T_A=25° C	-	5.5	-	ms
		External crystal, V_{DD} = 5.5 V, f_{OSC} = 6 MHz, T_A=-40° C	-	-	8	ms
		External crystal, V_{DD} = 5.0 V, f_{OSC} = 6 MHz, T_A=25° C	-	3.3	-	ms
		External crystal, V_{DD} = 5.5 V, f_{OSC} = 8 MHz, T_A=-40° C	-	-	7	ms
		External crystal, V_{DD} = 5.0 V, f_{OSC} = 8 MHz, T_A= 25° C	-	2.7	-	ms

4.3.4 EMC characteristics

Susceptibility tests are performed on a sample basis during product characterization.

Functional EMS (electromagnetic susceptibility)

Based on a simple running application on the product (toggling 2 LEDs through I/O ports), the product is stressed by two electromagnetic events until a failure occurs (indicated by the LEDs).

- **ESD**: Electrostatic discharge (positive and negative) is applied on all pins of the device until a functional disturbance occurs. This test conforms with the IEC 1000-4-2 standard.
- **FTB**: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test conforms with the IEC 1000-4-4 standard.

A device reset allows normal operations to be resumed. The test results are given in the table below based on the EMS levels and classes defined in application note AN1709.

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations:

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical data corruption (control registers...)

Prequalification trials:

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the RESET pin or the oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Table 19. EMS data

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD}=5 V, T_A=+25° C, f_{MCLK}=36 MHz conforms to IEC 1000-4-2	4A
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD}=5 V, T_A=+25° C, f_{MCLK}=36 MHz conforms to IEC 1000-4-4	4A

Output driving current

Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

Table 24. Output driving current

I/O Type	Symbol	Parameter	Conditions	Min	Max	Unit
Standard	V_{OL} 1)	Output low level voltage for an I/O pin when 8 pins are sunk at same time	I_{IO}=+2 mA		0.4	V
	V_{OH} 2)	Output high level voltage for an I/O pin when 4 pins are sourced at same time	I_{IO}=-2 mA	V_{DD}-0.8		
Med. Current (JTDO)	V_{OL} 1)	Output low level voltage for an I/O pin	I_{IO}=+6 mA		0.4	
	V_{OH} 2)	Output high level voltage for an I/O pin	I_{IO}=-6 mA	V_{DD}-0.8		
High Current P6.0	V_{OL} 1)	Output low level voltage for an I/O pin	I_{IO}=+8 mA		0.4	
	V_{OH} 2)	Output high level voltage for an I/O pin	I_{IO}=-8 mA	V_{DD}-0.8		

1. The I_{IO} current sunk must always respect the absolute maximum rating specified in *Table 6* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.
2. The I_{IO} current sourced must always respect the absolute maximum rating specified in *Table 6* and the sum of I_{IO} (I/O ports and control pins) must not exceed IV_{DD}.

Figure 13. V_{OH} standard ports vs I_{OH} @ V_{DD} 5V T_A -45° C

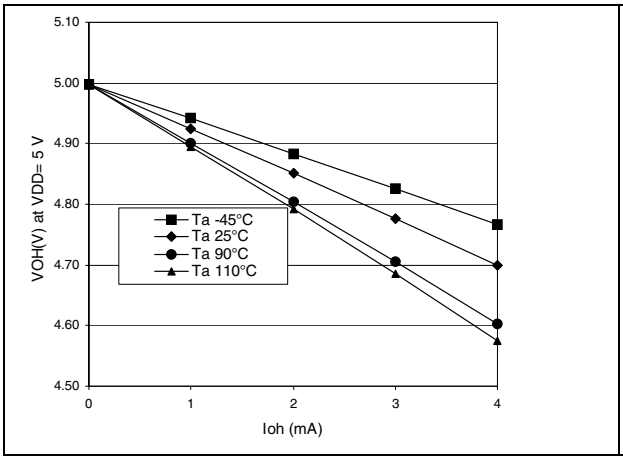
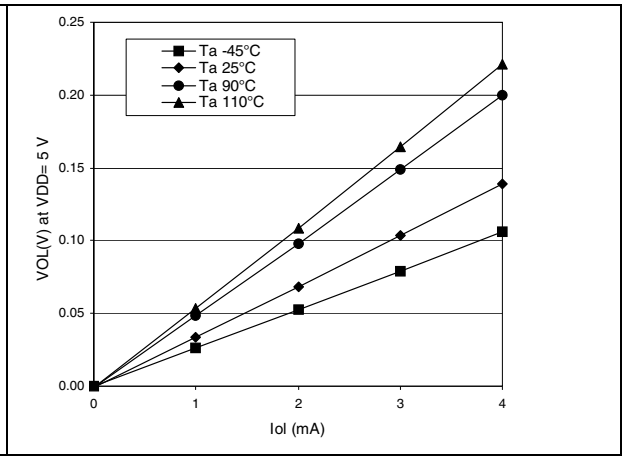


Figure 14. V_{OL} standard ports vs I_{OL} @ V_{DD} 5 V



NRSTIN pin

The NRSTIN pin input driver is CMOS. A permanent pull-up is present which is the same as R_{PU} (see *: General characteristics on page 38*)

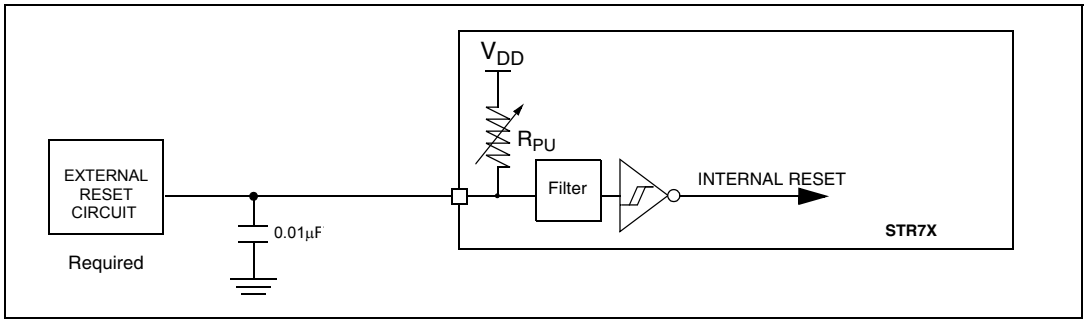
Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

Table 25. Reset pin characteristics

Symbol	Parameter	Conditions	Min	Typ [1]	Max	Unit
$V_{IL(NRSTIN)}$	NRSTIN Input low level voltage [1]				0.3 V_{DD}	V
$V_{IH(NRSTIN)}$	NRSTIN Input high level voltage [1]		0.7 V_{DD}			
$V_{hys(NRSTIN)}$	NRSTIN Schmitt trigger voltage hysteresis [2]			800		mV
$V_{F(RSTINn)}$	NRSTIN Input filtered pulse[3]				500	ns
$V_{NF(RSTINn)}$	NRSTIN Input not filtered pulse[3]		2			µs
$V_{RP(RSTINn)}$	NRSTIN removal after Power-up[3]		100			µs

1. Data based on characterization results, not tested in production.
2. Hysteresis voltage between Schmitt trigger switching levels.
3. Data guaranteed by design, not tested in production.

Figure 19. Recommended NRSTIN pin protection[1]



1. The R_{PU} pull-up equivalent resistor is based on a resistive transistor.
2. The reset network protects the device against parasitic resets.
3. The user must ensure that the level on the NRSTIN pin can go below the $V_{IL(NRSTIN)}$ max. level specified in *Table 25*. Otherwise the reset will not be taken into account internally.

Figure 20. NRSTIN R_{PU} vs. V_{DD}

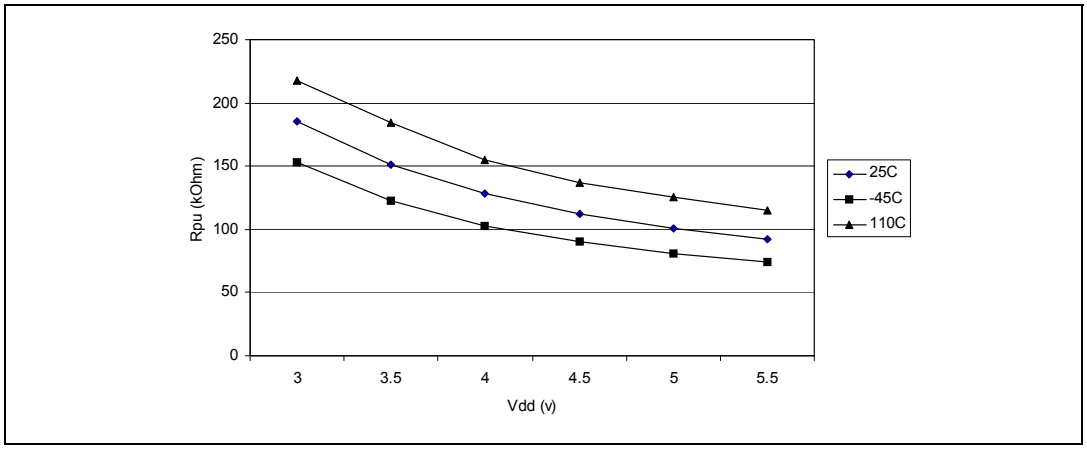


Table 27. ADC accuracy with f_{MCLK} = 20 MHz, f_{ADC}=10 MHz, R_{AIN} < 10 kΩ RAIN, V_{DDA}=5 V. This assumes that the ADC is calibrated[2)]

Symbol	Parameter	Conditions	Typ	Max	Unit
$\|E_T\|$	Total unadjusted error [1)]		1.0	2.0	LSB
$\|E_O\|$	Offset error [1)]		0.15	1.0	
$\|E_G\|$	Gain error [1)]		0.97	1.1	
$\|E_D\|$	Differential linearity error[1)]		0.7	1.0	
$\|E_L\|$	Integral linearity error [1)]		0.76	1.5	

1. ADC accuracy vs. negative injection current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current. The effect of negative injection current on robust pins is specified in *Section 4.3.5*.
   Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 4.3.5* does not affect the ADC accuracy.
2. Calibration is needed once after each power-up.

Figure 21. ADC accuracy characteristics

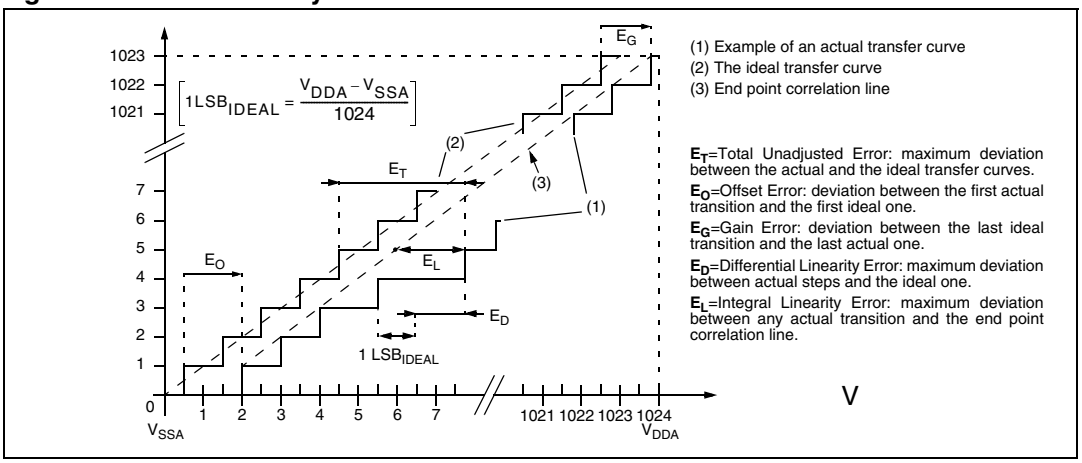
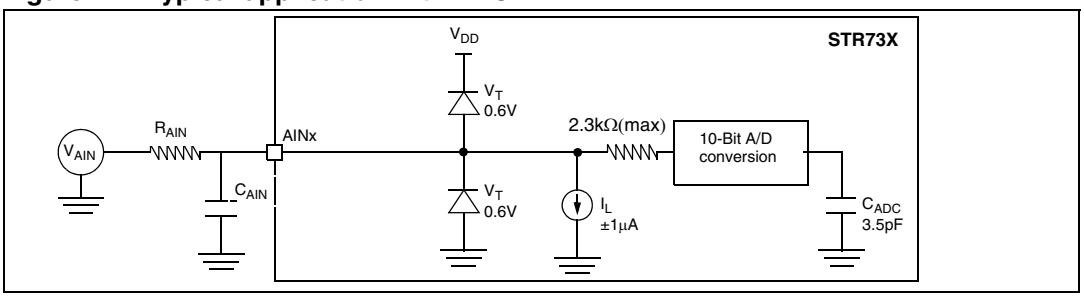


Figure 22. Typical application with ADC



Analog power supply and reference pins

The V_{DDA} and V_{SSA} pins are the analog power supply of the A/D converter cell. They act as the high and low reference voltages for the conversion.

Separation of the digital and analog power pins allow board designers to improve A/D performance. Conversion accuracy can be impacted by voltage drops and noise in the event of heavily loaded or badly decoupled power supply lines (see*: General PCB design guidelines*).

General PCB design guidelines

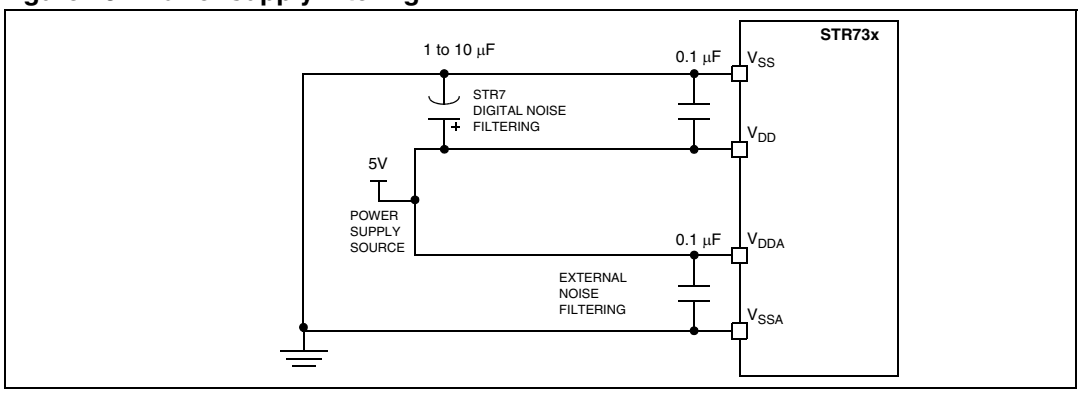
To obtain best results, some general design and layout rules should be followed when designing the application PCB to shield the noise-sensitive, analog physical interface from noise-generating CMOS logic signals.

- Use separate digital and analog planes. The analog ground plane should be connected to the digital ground plane via a single point on the PCB.
- Filter power to the analog power planes. It is recommended to connect capacitors, with good high frequency characteristics, between the power and ground lines, placing 0.1 µF and optionally, if needed 10 pF capacitors as close as possible to the STR7 power supply pins and a 1 to 10 µF capacitor close to the power source (see *Figure 23*).
- The analog and digital power supplies should be connected in a star network. Do not use a resistor, as V_{DDA} is used as a reference voltage by the A/D converter and any resistance would cause a voltage drop and a loss of accuracy.
- Properly place components and route the signal traces on the PCB to shield the analog inputs. Analog signals paths should run over the analog ground plane and be as short as possible. Isolate analog signals from digital signals that may switch while the analog inputs are being sampled by the A/D converter. Do not toggle digital outputs near the A/D input being converted.

Software filtering of spurious conversion results

For EMC performance reasons, it is recommended to filter A/D conversion outliers using software filtering techniques.

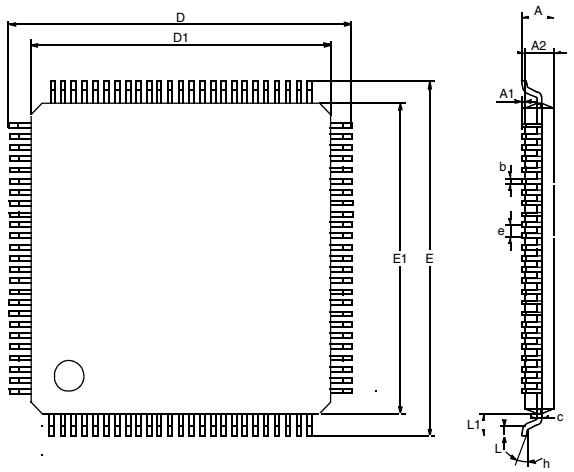
Figure 23. Power supply filtering



5 Package characteristics

5.1 Package mechanical data

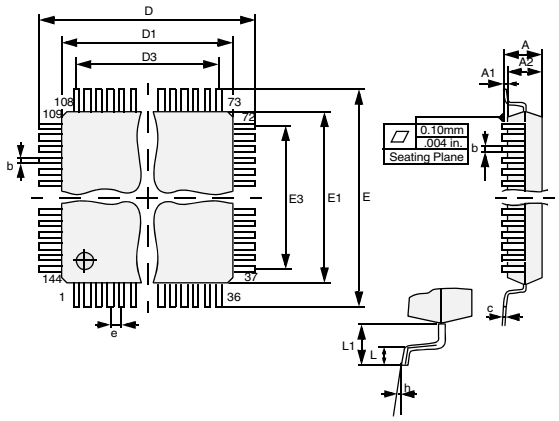
Figure 24. 100-pin thin quad flat package



Dim.	mm			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A			1.60			0.0630
A1	0.05		0.15	0.0020		0.0059
A2	1.35	1.40	1.45	0.0531	0.0551	0.0571
b	0.17	0.22	0.27	0.0067	0.0087	0.0106
C	0.09		0.20	0.0035		0.0079
D		16.00			0.6299	
D1		14.00			0.5512	
E		16.00			0.6299	
E1		14.00			0.5512	
e		0.50			0.0197	
h	0°	3.5°	7°	0°	3.5°	7°
L	0.45	0.60	0.75	0.0177	0.0236	0.0295
L1		1.00			0.0394	
	Number of Pins					
N	100					

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 25. 144-pin thin quad flat package



Dim.	mm			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A			1.60			0.0630
A1	0.05		0.15	0.0020		0.0059
A2	1.35	1.40	1.45	0.0531	0.0551	0.0571
b	0.17	0.22	0.27	0.0067	0.0087	0.0106
c	0.09		0.20	0.0035		0.0079
D	21.80	22.00	22.20	0.8583	0.8661	0.8740
D1	19.80	20.00	20.20	0.7795	0.7874	0.7953
D3		17.50			0.6890	
E	21.80	22.00	22.20	0.8583	0.8661	0.8740
E1	19.80	20.00	20.20	0.7795	0.7874	0.7953
E3		17.50			0.6890	
e		0.50			0.0197	
K	0°	3.5°	7°	0°	3.5°	7°
L	0.45	0.60	0.75	0.0177	0.0236	0.0295
L1		1.00			0.0394	
	Number of Pins					
N	144					

1. Values in inches are converted from mm and rounded to 4 decimal digits.

8 Revision history

Table 30. Document revision history

Date	Revision	Description of changes
19-Sep-2005	1	First release
02-Nov-2005	2	Removed Table 8 power consumption in LP modes Updated PLL frequency in *Section 1.1* and *Table 12*
08-Mar-2006	3	*Section 3.4: Preliminary power consumption data* updated *Section 3.5: DC electrical characteristics* updated *Section 7: Known limitations* added
04-Jun-2006	4	*Section 4: Electrical parameters* updated *Section 7: Known limitations* updated Added temperature range -40°C to 85°C in *Section 6: Order codes*
19-Jun-2006	5	Changed Flash data retention to 20 years at 85°C in *Table 18 on page 34*.
08-Sep-2006	6	Changed *Table 24: Output driving current on page 39* Added *Figure 14: VOL standard ports vs IOL @ VDD 5 V* thru *Figure 18: VOL P6.0 pin vs IOL @ VDD 5 V on page 40*. Added *Figure 20: NRSTIN RPU vs. VDD*
08-Jun-2008	7	Inch values rounded to 4 decimal digits in *Section 5.1: Package mechanical data* Modified BSPI speed in *Section 2.1: On-chip peripherals*